



**DMN3730UFB**

**30V N-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
30V	460mΩ @ $V_{GS} = 4.5V$	0.9A
	560mΩ @ $V_{GS} = 2.5V$	0.7A

**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Load switch
- Portable applications
- Power Management Functions

**Features and Benefits**

- 0.5mm ultra low profile package for thin application
- 0.6mm<sup>2</sup> package footprint, 10 times smaller than SOT23
- Low  $V_{GS(th)}$ , can be driven directly from a battery
- Low  $R_{DS(on)}$
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- ESD Protected Gate 2kV
- Qualified to AEC-Q101 Standards for High Reliability

**Mechanical Data**

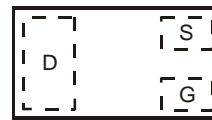
- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)



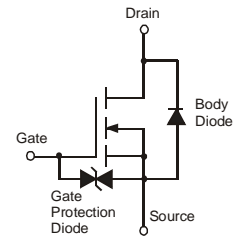
DFN1006-3



Bottom View



Top View  
Internal Schematic



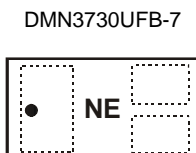
Equivalent Circuit

**Ordering Information** (Note 3)

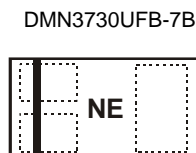
Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3730UFB-7	NE	7	8	3,000
DMN3730UFB-7B	NE	7	8	10,000

- Notes:
1. No purposefully added lead
  2. Diodes Inc's "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**



Top View  
Dot Denotes  
Drain Side



Top View  
Bar Denotes Gate  
and Source Side

NE = Product Type Marking Code

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	30	V
Gate-Source Voltage		V <sub>GSS</sub>	±8	
Continuous Drain Current	V <sub>GS</sub> = 4.5V	(Note 5)	0.91	A
		T <sub>A</sub> = 70°C (Note 5)	0.73	
		(Note 4)	0.75	
Pulsed Drain Current		I <sub>DM</sub>	3	A

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P <sub>D</sub>	0.69	W
	(Note 4)		0.47	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	180	°C/W
	(Note 4)		258	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	3	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.45	-	0.95	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(on)</sub>	-	-	460	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA
				560		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 100mA
				730		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 75mA
Forward Transfer Admittance	Y <sub>fs</sub>	40	-	-	mS	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	-	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 300mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	-	64.3	-	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	6.1	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	4.5	-	pF	
Gate Resistance	R <sub>g</sub>	-	70	-	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	-	1.6	-	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 1A
Gate-Source Charge	Q <sub>gs</sub>	-	0.2	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>	-	0.2	-	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	3.5	-	ns	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1A V <sub>GS</sub> = 10V, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	-	2.8	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	38	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	13	-	ns	

- Notes:
4. For a device surface mounted on a minimum recommended pad layout of an FR4 PCB, in still air conditions; the device is measured when operating in steady-state condition.
  5. Same as note 4, except the device measured at t ≤ 10 sec.
  6. Same as note 4, except the device is pulsed at duty cycle of 1% for a pulse width of 10μs.
  7. Measured under pulsed conditions to minimize self-heating effect. Pulse width ≤ 300μs; duty cycle ≤ 2%
  8. For design aid only, not subject to production testing.

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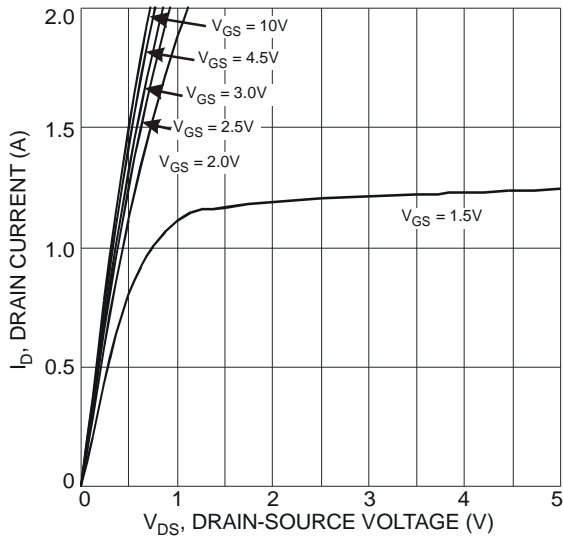


Fig. 1 Typical Output Characteristic

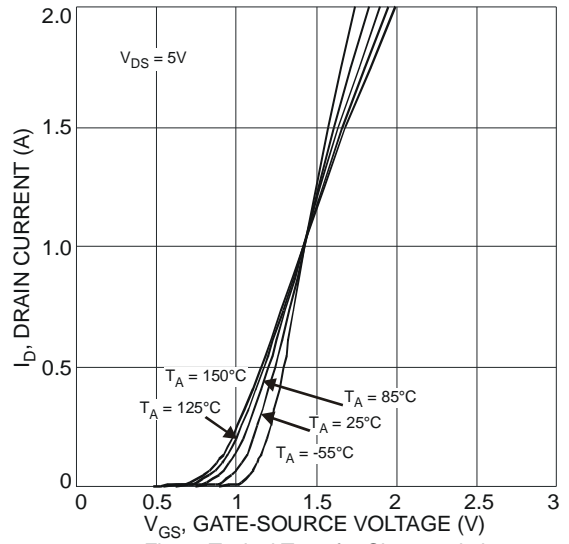


Fig. 2 Typical Transfer Characteristic

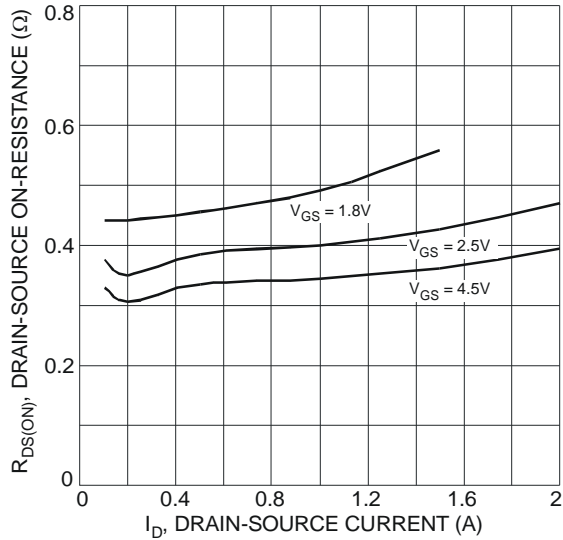


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

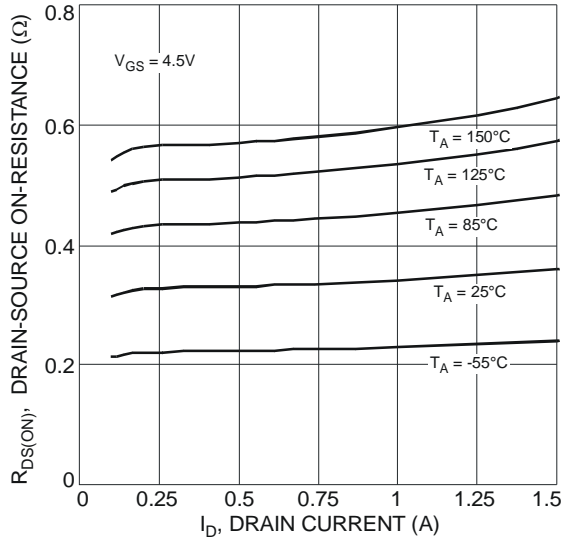


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

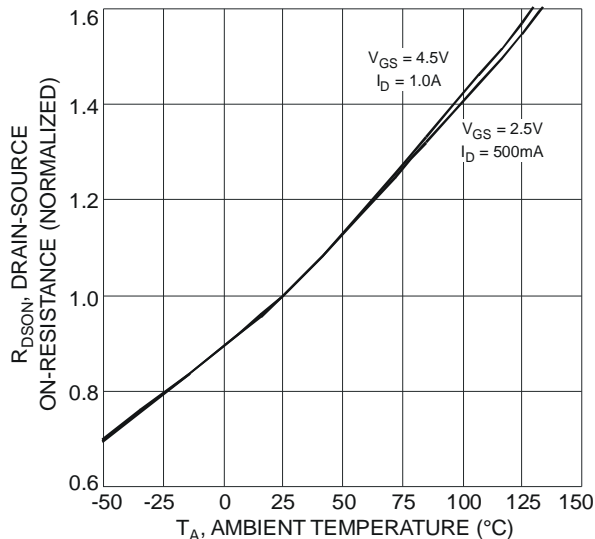


Fig. 5 On-Resistance Variation with Temperature

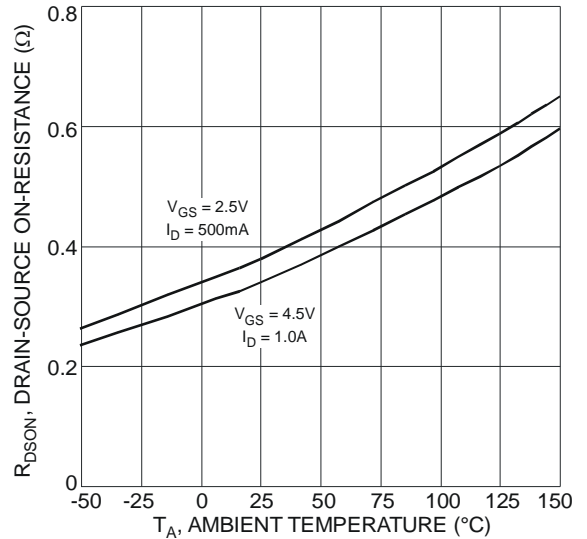


Fig. 6 On-Resistance Variation with Temperature

**DMN3730UFB**

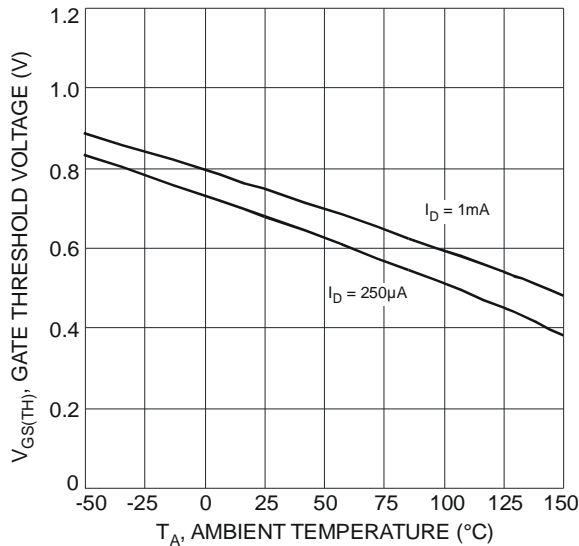


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

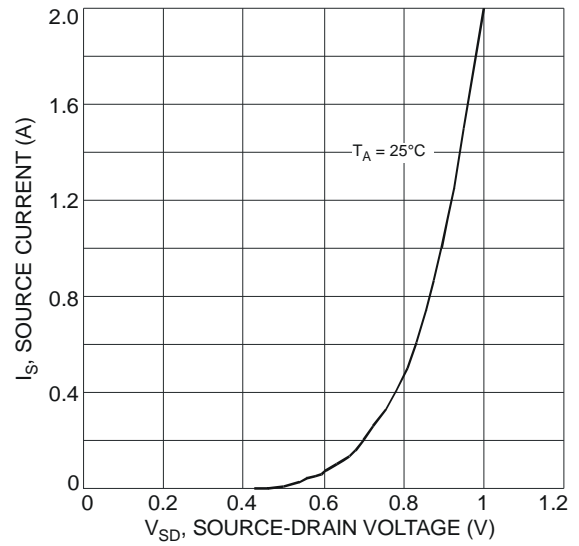


Fig. 8 Diode Forward Voltage vs. Current

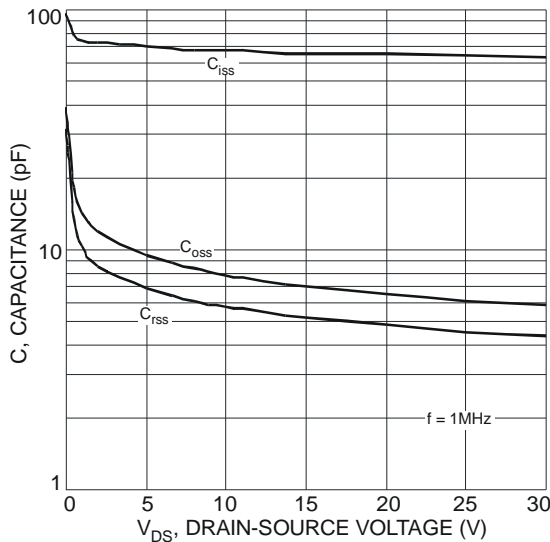


Fig. 9 Typical Total Capacitance

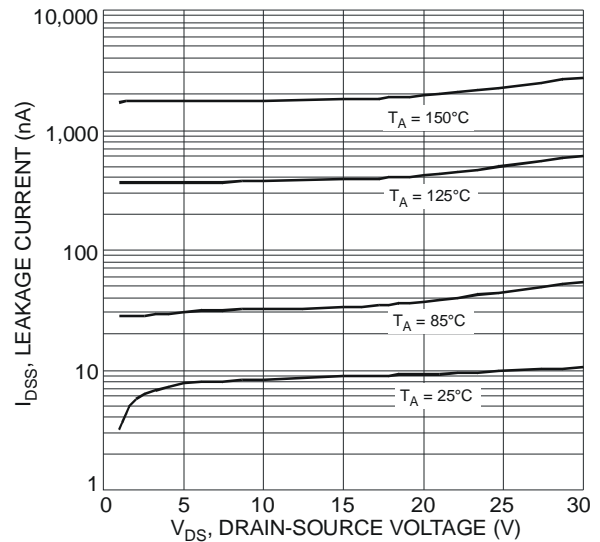


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

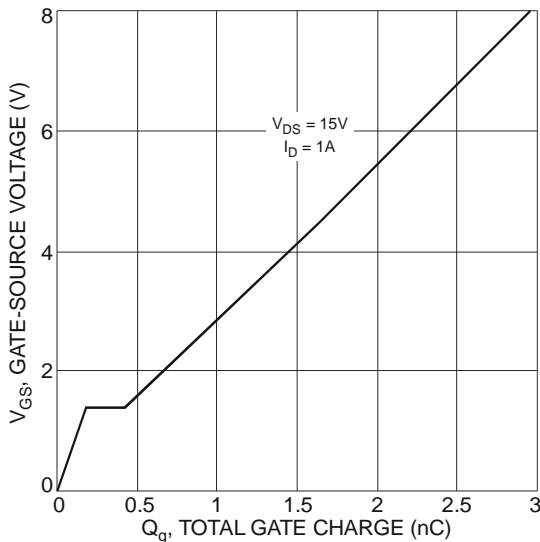


Fig. 11 Gate-Charge Characteristics

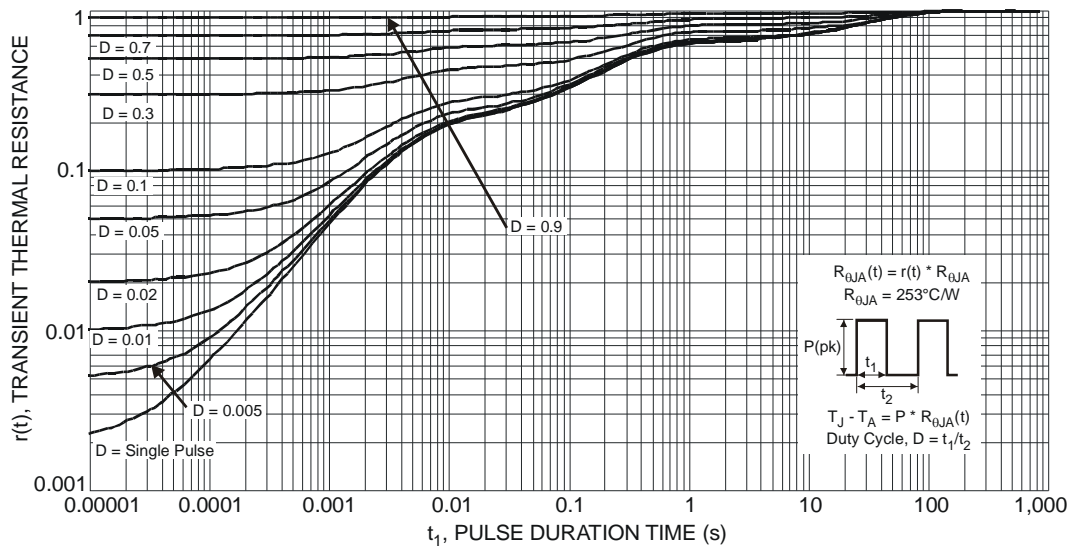
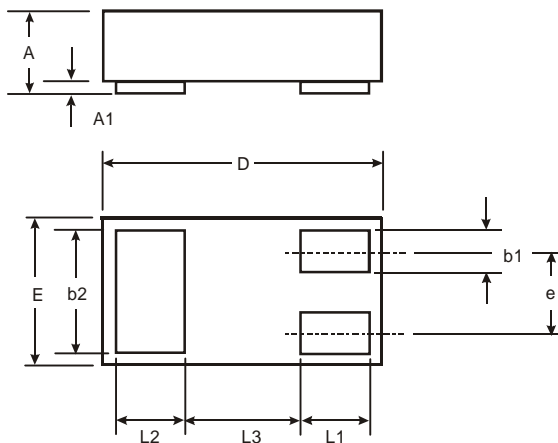


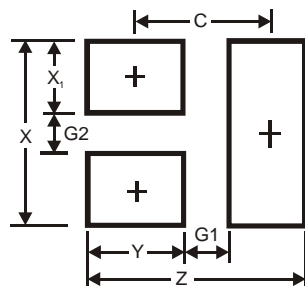
Fig. 12 Transient Thermal Response

**Package Outline Dimensions**



DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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